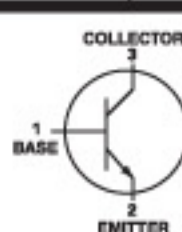


**NPN General Purpose Transistors**

**SOT-23**
**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CE0}$	25	Vdc
Collector-Base Voltage	$V_{CBO}$	40	Vdc
Emitter-Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current-Continuous	$I_C$	1500	mAdc

**THERMAL CHARACTERISTICS**

Characteristics	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (1) $T_A=25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	1.8	$\text{mW}/^\circ\text{C}$
Total Device Dissipation Alumina Substrate, (2) $T_A=25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	5.0	$\text{mW}/^\circ\text{C}$
Junction and Storage, Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

**DEVICE MARKING**

SS8050=Y1

**ELECTRICAL CHARACTERISTICS**

Characteristics	Symbol	Min	Max	Unit
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**OFF CHARACTERISTICS**

Collector-Emitter Breakdown Voltage ( $I_C=0.1\text{mA}, I_B=0$ )	$V_{(BR)CEO}$	25	-	Vdc
Collector-Base Breakdown Voltage ( $I_C=100\mu\text{A}, I_E=0$ )	$V_{(BR)CBO}$	40	-	Vdc
Emitter-Base Breakdown Voltage ( $I_E=100\mu\text{A}, I_C=0$ )	$V_{(BR)EBO}$	6.0	-	Vdc
Collector Cutoff Current ( $V_{CE}=20\text{Vdc}, I_E=0$ )	$I_{CEO}$	-	0.1	$\mu\text{A}$
Collector Cutoff Current ( $V_{CB}=40\text{Vdc}, I_E=0$ )	$I_{CBO}$	-	0.1	$\mu\text{A}$
Emitter Cutoff Current ( $V_{EB}=5.0\text{Vdc}, I_C=0$ )	$I_{EBO}$	-	0.1	$\mu\text{A}$

1.FR-5=1.0 x 0.75 x 0.062 in

2.Alumina=0.4 x 0.3 x 0.024 in. 99.5% alumina

**SS8050**

**ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$  unless otherwise noted) (Continued)**

Characteristics	Symbol	Min	Max	Unit
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**ON CHARACTERISTICS**

DC Current Gain ( $I_C=100\text{mA}, V_{CE}=1.0\text{Vdc}$ ) ( $I_C=800\text{mA}, V_{CE}=1.0\text{Vdc}$ )	$h_{FE}^{(1)}$ $h_{FE}^{(2)}$	120 40	350 -	- -
Collector-Emitter Saturation Voltage ( $I_C=800\text{mA}, I_B=80\text{mA}$ )	$V_{CE(sat)}$	-	0.5	Vdc
Base-Emitter Saturation Voltage ( $I_C=800\text{mA}, I_B=80\text{mA}$ )	$V_{BE(sat)}$	-	1.2	Vdc

**SMALL-SIGNAL CHARACTERISTICS**

Current-Gain-Bandwidth Product ( $I_C=50\text{mA}, V_{CE}=10\text{Vdc}, f=30\text{MHz}$ )	$f_T$	100	-	MHz
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**CLASSIFICATION OF  $h_{FE}$** 

Rank	L	H
Range	120-200	200-350

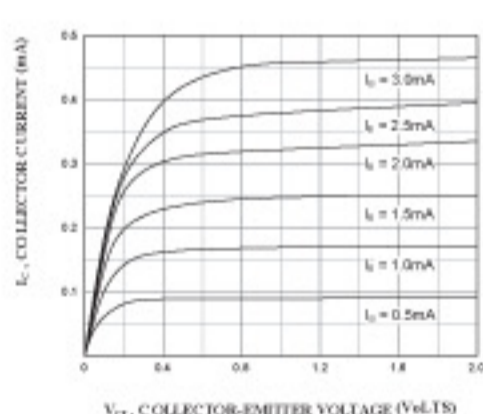
**SS8050**


Figure 1. Static Characteristic

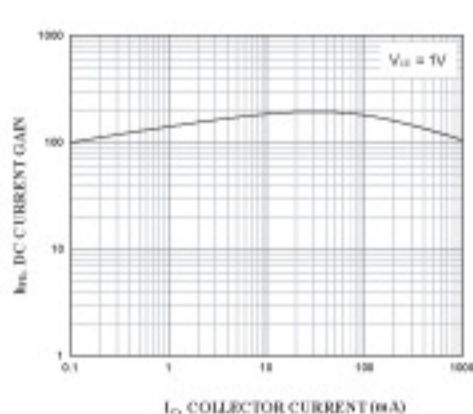


Figure 2. DC current Gain

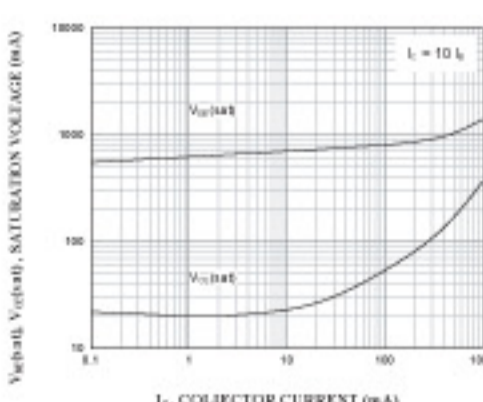
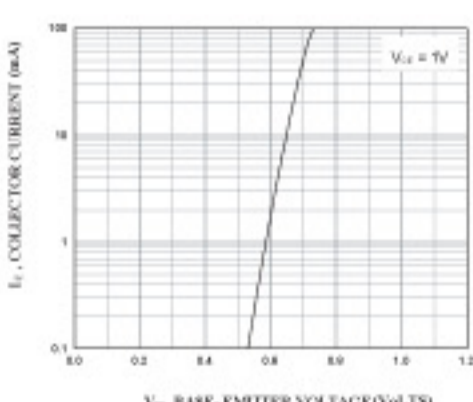

 Figure 3. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage


Figure 4. Base-Emitter On Voltage

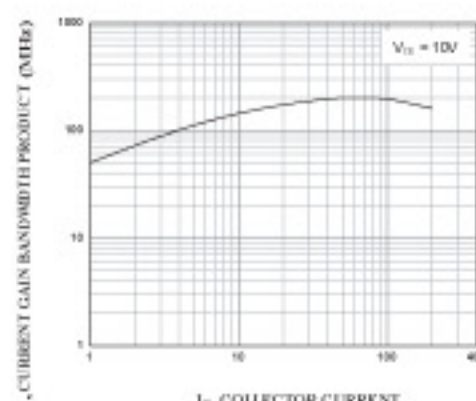


Figure 5. Current Gain Bandwidth Product